



Getting ready for RF MEMS GEO flight demonstration

O. Vendier, C. Drevon, JL. Cazaux, P-L Charvet¹, J-P Polizzi¹, C. Zanchi², F. Courtade², F. Presseqc²

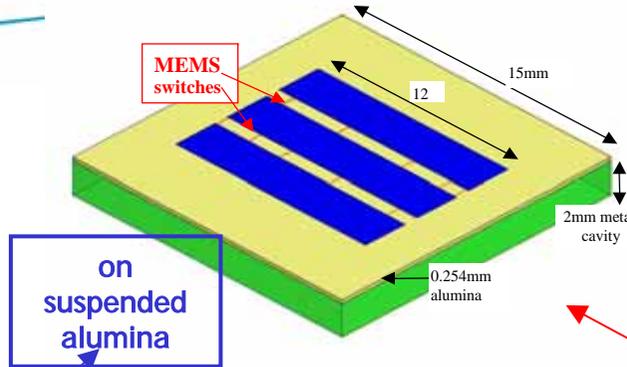
(1) CEA LETI MINATECH

(2) CNES

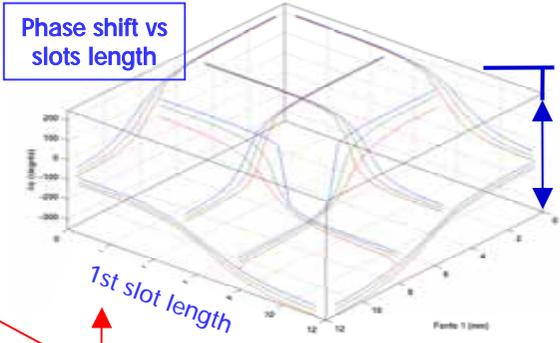
THALES

- Introduction
- Mission/experience presentation
- Description of the equipment constituents
 - Mechanical overview
 - TMTC
 - FPGA and dedicated ASIC
 - MEMS based hybrids
- EM manufacturing and test
- Conclusion and perspectives

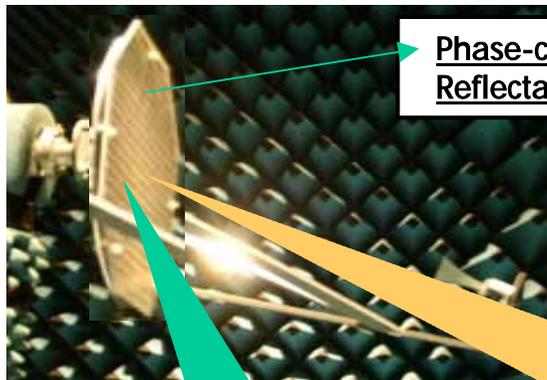
MEMS-controlled ReflectArray



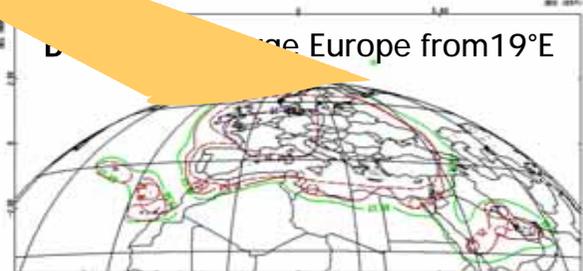
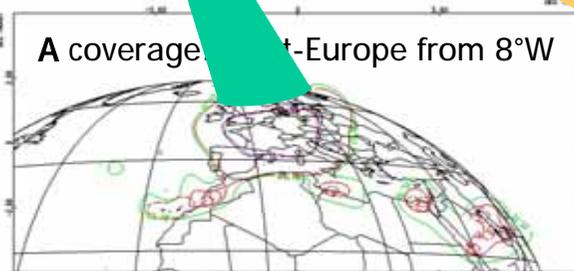
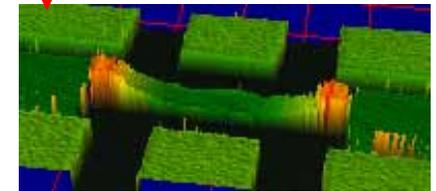
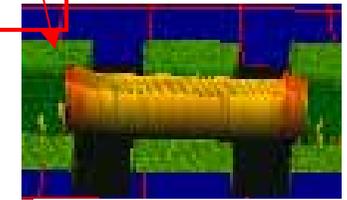
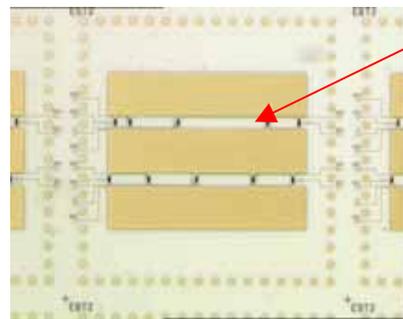
Phase shift vs slots length



on suspended alumina



on thinned silicon

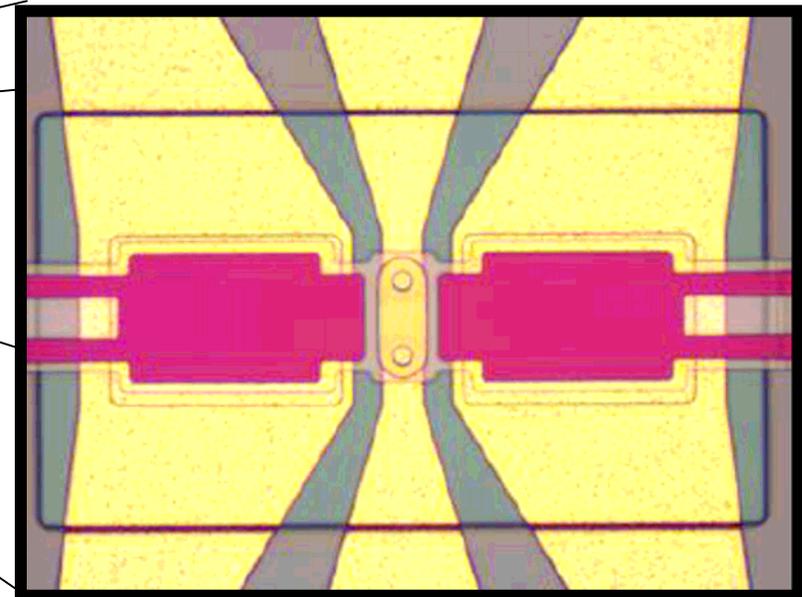
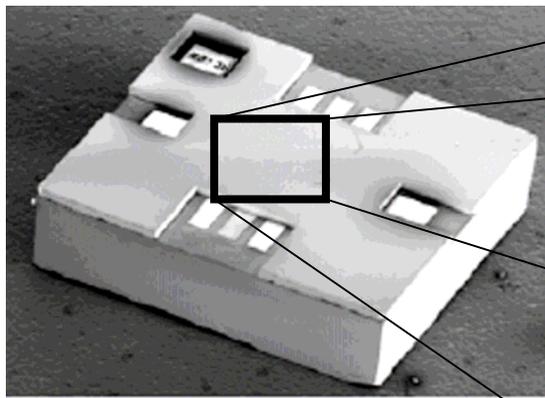


TAS-F + LETI, LAAS

Typical power-handling: 2 to 4 W per reflecting cell **1 to 2 W max through 1 switch** in worst case states of the 10 controllable ones

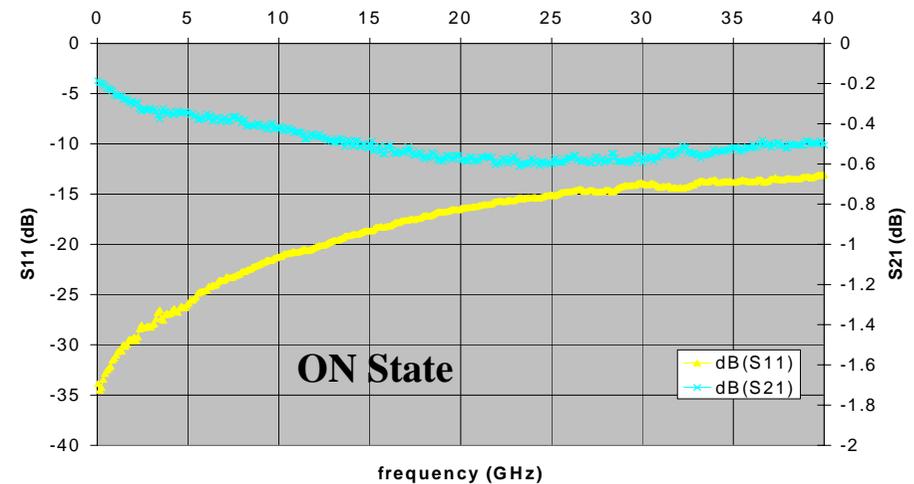
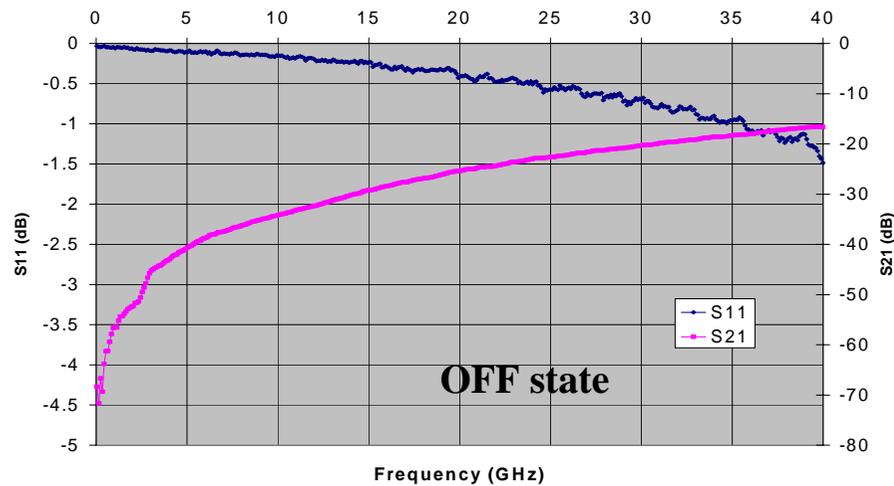
- Visibility of the new technology vs future customers
 - Internal
 - External
- Go from mid to high TRL
 - Refine design/test methodology applicable to flight models
 - Documentation
 - Industrialisation approach
- Enhance know-how of the new technology
 - Use into industrial environment
 - Technology integrated into flight proven technologies
 - Risk assessment
- Qualification of the available technology prior to flight demonstration

- CNES contract
- Thales Alenia Space : Prime contractor, design, manufacturing and test of the demonstrator
- RF MEMS technology
 - Ohmic switch technology from CEA LETI



- Technology qualification
 - Technical support from CNES at component level
 - TAS in-house capability

Ohmic contact, serie switch from CEA-LETI (after flip-chip mounting)



■ Comparaison with a standard diode (Diode beam lead HPND 4005)

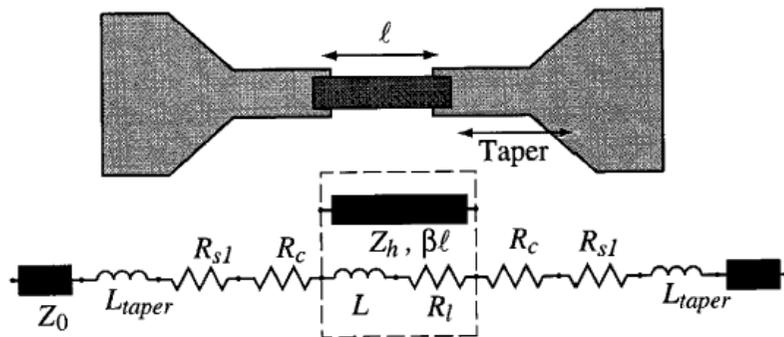
| | Pertes de transmission : Etat ON à 30 GHz | Isolation : Etat OFF à 30 GHz | RON | COFF | 1/(RON,COFF) |
|-------|---|-------------------------------|----------|--------|--------------|
| MEMS | 0,29 dB | 19,9 dB | 1,7 ohms | 9,8 fF | 60 THz |
| Diode | 0,76 dB | 8,9 db | 5 ohms | 22 fF | 9 THz |

Base for demonstrator definition

- Observed failure mode for ohmic contact switches
 - Contact :
 - Contact degradation
 - *Stiction metal-metal*
 - Membrane :
 - Residual stress, stress gradient, thermal stress
 - *Creep*
 - Electrostatic activation
 - Dielectric charging

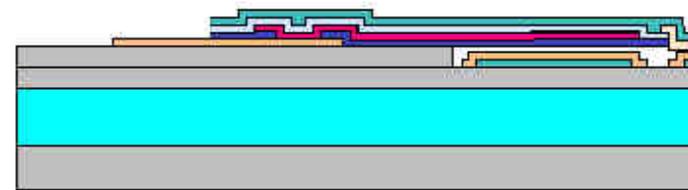
Basement for experiment definition

- Based on DC parameters
 - Fundamental sollicitation modes
 - Application (redundancy, fast switching)
 - Advanced RF switch intrinsic characteristics : R_c (On) et V_p



$$R_s = 2R_c + 2R_{sl} + R_l$$

$$pertes = \frac{4R_s Z_0}{|Z_s + 2Z_0|^2}$$



↕ g = gap

$$V_p = \sqrt{\frac{8k}{27\varepsilon_0 W w}} g_0^{3/2}$$

Membrane spring constant

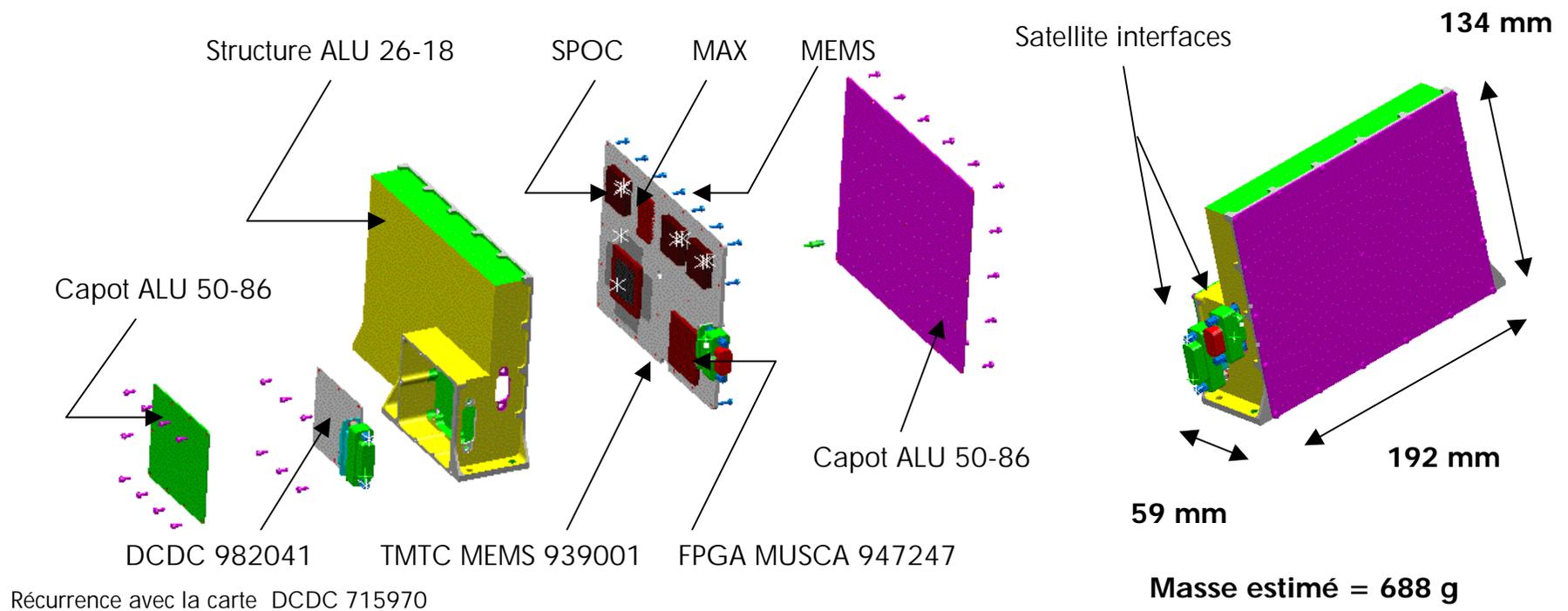
$$k = 4Ew \left(\frac{t}{l} \right)^3$$

| <i>Measured characteristics</i> | <i>Static performances</i> | <i>RF performances</i> | <i>Impact on reliability assessment</i> |
|---|--|---|--|
| Number of cycles with various profile | N/A | N/A | - Reliability rough figure - Effect according to cycling profile |
| Series resistance of the switch (R_s) | Contact resistance (R_c) derived from analytic equation ⁽²⁾ | S_{12} is derived from equation : insertion loss ⁽¹⁾ | - Contact aging (pollution, tribology, radiations,...) - stiction, microsoldering,... |
| Pull-in voltage (V_p) | At known material characteristics, can be calculated (k) ⁽⁴⁾ and derived gap (g_0) ⁽³⁾ | S_{12} is derived from EM 3D model : isolation | - Membrane deformation |

- Mode INIT: all the MEMS are switched On/Off 5 times, launched by TC
- Mode(1) : MEMS aging due to On/Off cycling, launched by TC
 - 1 Cycle On/Off per second : 4 MEMS
 - 1 Cycle On/Off per day : 4 MEMS
 - 1 Cycle On/Off per year : 4 MEMS
- Mode(2) : MEMS aging with sollicitation close to redundancy application
 - TC launched switch : 4 MEMS .
- Mode(4): Pull-in/Pull-out measurements
 - TC launched sequence : 4 MEMS
- Temperature monitoring

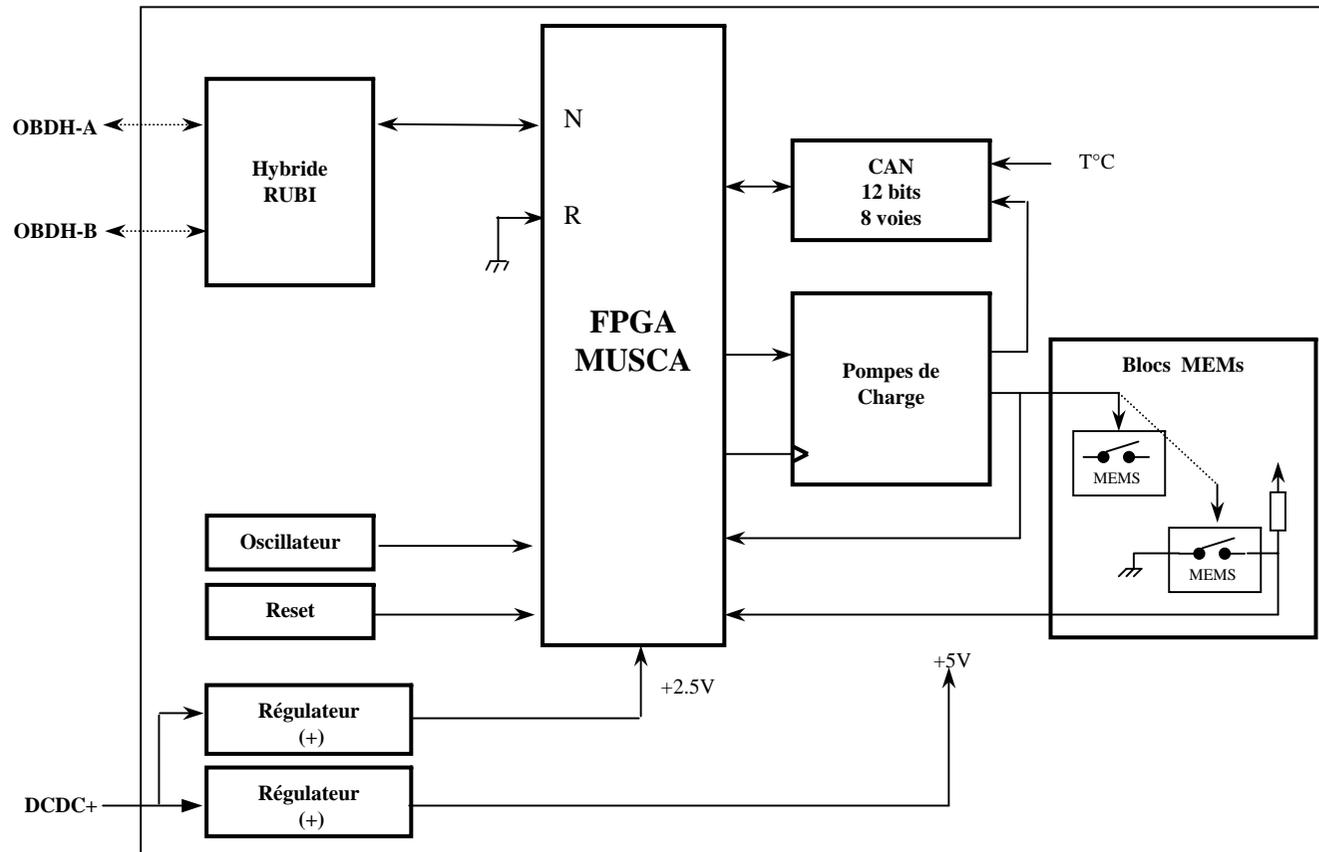
Demonstrator is composed of 2 PCBs : 1 DCDC et 1 TMTc/MEMS

- Mono-structure in Al with 2 caps.
- Interfaces to satellite platform by Sub-D connectors (15pts DCDC et 9pts TMTc)



Main functions realized by TMTC building block:

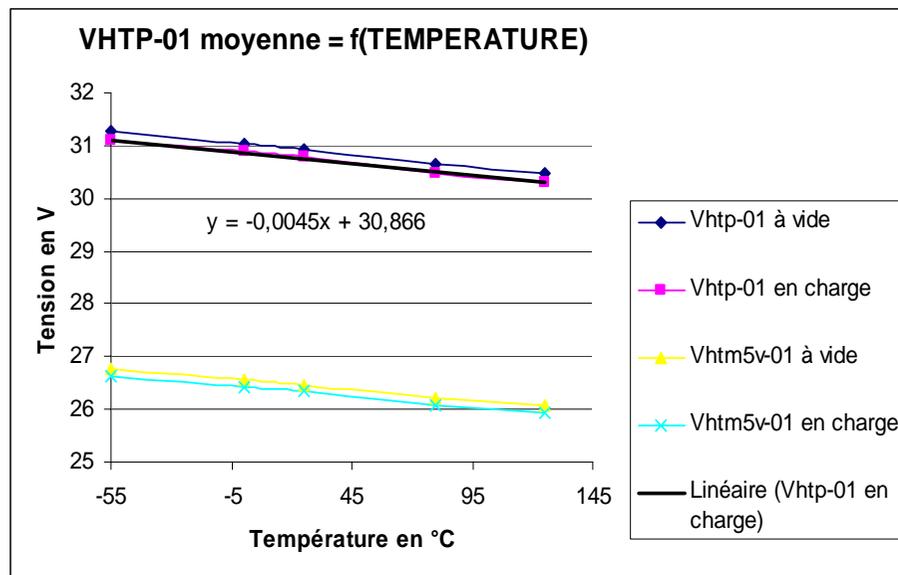
- Interface with SB4000 bus OBDH 485
 - Regulated biasing generation based on DCDC provided voltage
 - Generation of clocks and test signals
 - Acquisition, management and processing of MEMS commands
 - Acquisition, management and processing of MEMS measurements
 - Generation of TM.
-
- This card is able to drive and monitor up to 5 charge pumps and up to 20 MEMS.



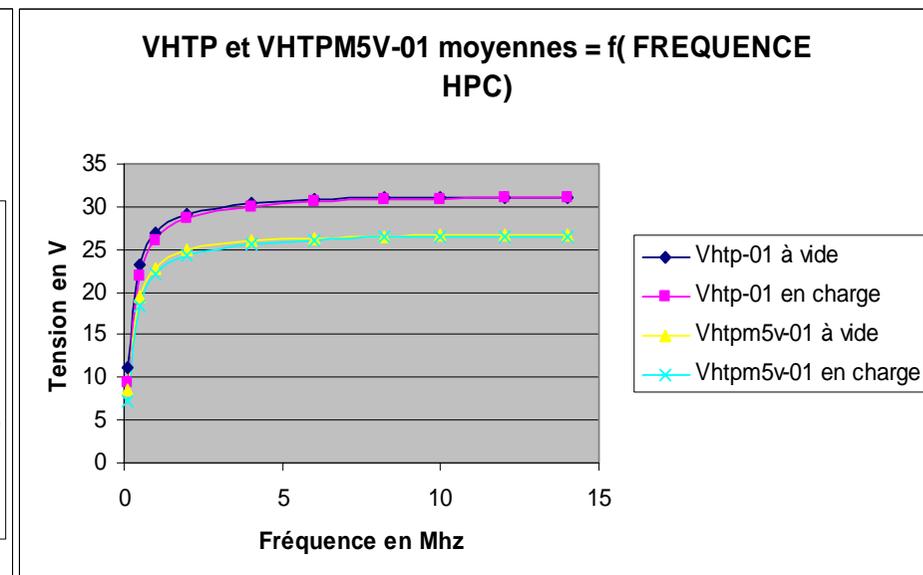
- Receive, decode, validation of serial bus ML16 coming from hybrid RUBI
- Management and treatment of data coming from RUBI through serial bus CS16
- Management of init procedure
- Management of MEMS through the charge pumps
- Management of the charge pumps (clocks, output voltage monitoring)
- Management of serial bus com/acq of 12 bits ADC
- Acquisition and treatment of data for TM
- Send TM on serial bus AS16 via RUBI.
- FPGA address set at 00000.

■ Robustness of the design, compliant with space constraints

Temperature stability

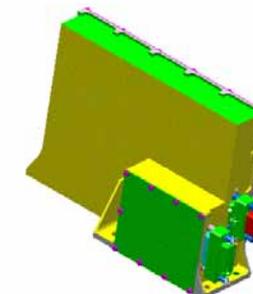
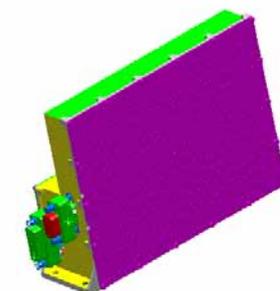


Stabilité en fréquence HPC



■ Packaged in hermetic ceramic package, qualified by lot

| SUB ASSEMBLY : | | | | | Total | | | Total |
|---------------------|------|-----------|-----|------------|------------|------------|-----------|------------|
| | | | | | Basic mass | | | Max mass |
| MEMS CNES | | | | | 625 | 10% | 63 | 688 |
| 938968 | | | | | | | | |
| Eléments | Date | Reference | Qty | Unit | Total | To lér, | Uncert. | Max mass |
| | | | | basic mass | basic mass | | | |
| | | | | (g) | (g) | (%) | (g) | (g) |
| Structure mécanique | | 938970 | 1 | 300 | 300 | 10% | 30 | 330 |
| Capot TMTC MEMS | | 938981 | 1 | 40 | 40 | 10% | 4 | 44 |
| Capot DCDC | | 938985 | 1 | 10 | 10 | 10% | 1 | 11 |
| Carte DCDC | | 982041 | 1 | 45 | 45 | 10% | 5 | 50 |
| Carte TMTC MEMS | | 939001 | 1 | 200 | 200 | 10% | 20 | 220 |
| Vis serie | | ** | 1 | 20 | 20 | 10% | 2 | 22 |
| Peinture | | ** | 1 | 10 | 10 | 10% | 1 | 11 |



Mechanical environment : SB4000 specification S000329 ed04

Zone A (1A+2A) : larger covering for P/L equipment

Sinus :

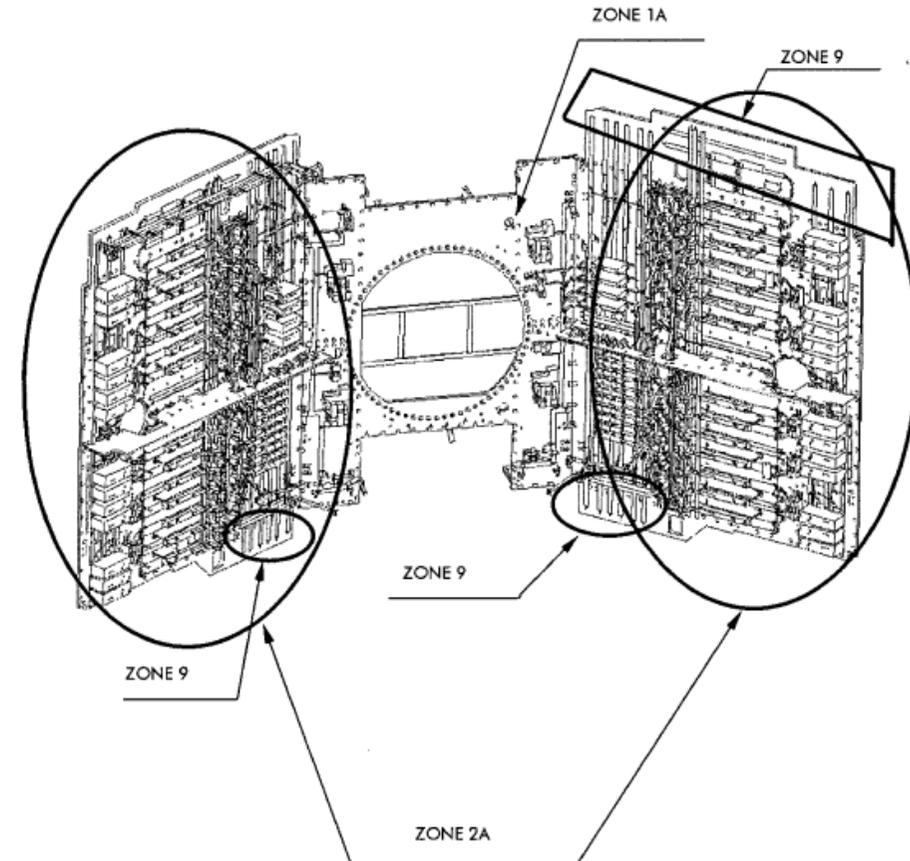
| Perpendicular to mounting plane (Z) | | parallel to mounting plane (X, Y) | |
|--|--------|--------------------------------------|--------|
| Range (Hz) | Level | Range (Hz) | Level |
| 5 - 21 | ±10 mm | 5 - 17 | ±10 mm |
| 21 - 100 | ± 18 g | 17 - 100 | ± 12 g |

Vibrations

| Perpendicular to the mounting plane (Z) | | Parallel to the mounting plane (X, Y) | |
|--|-------------------------|--|-------------------------|
| Range (Hz) | PSD Level | Range (Hz) | PSD Level |
| 20 - 50 | + 6 dB/oct | 20 -100 | + 6 dB/oct |
| 50 - 350 | 0.8 g ² /Hz | 100 - 500 | 0.1 g ² /Hz |
| 350 - 447 | - 12 dB/oct | 500 - 2000 | 0.05 g ² /Hz |
| 447 - 1000 | 0.3 g ² /Hz | | |
| 1000 - 1565 | - 12 dB/oct | | |
| 1565 - 2000 | 0.05 g ² /Hz | | |
| Global : 23.76 g RMS | | Global : 10.9 g RMS | |

Shocks : Zone S4

| Frequency (Hz) | Qualification Shock Response (g) / Q = 10 |
|----------------|---|
| 500 | 200 |
| 3000 | 2000 |
| 10000 | 2000 |



•**Thermal environment:** SB4000 specification S000329 ed04

Environment RX TTC

| | Operating mode | |
|---------------|----------------|-------------|
| | T min. (°C) | T max. (°C) |
| Qualification | -30 | +70 |
| Acceptance | -25 | +65 |

Equipment with black paint : emissivity of 0.85

Start up cold : -35°C Qualif et -30°C Acceptance

Dissipated power for TMTC = 1.24W typical

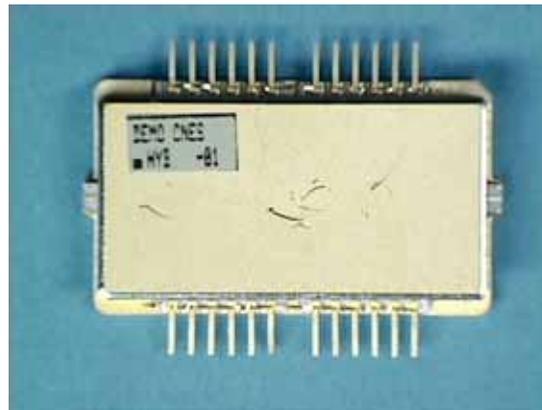
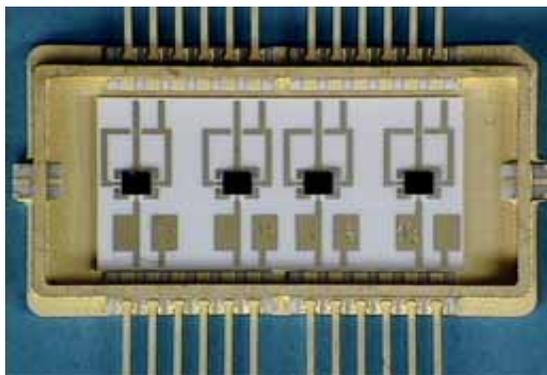
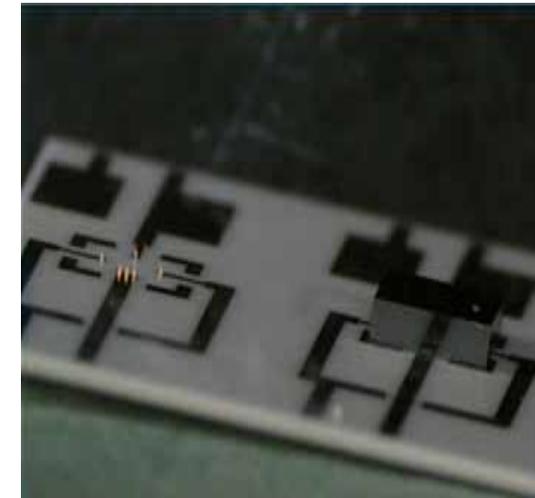
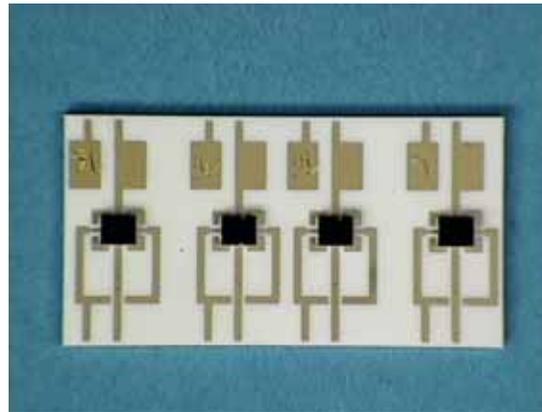
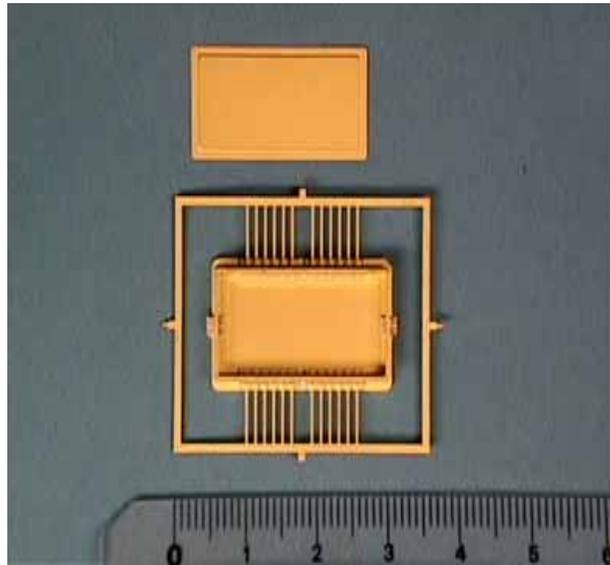
Dissipated power for DCDC = 0.56 W typical

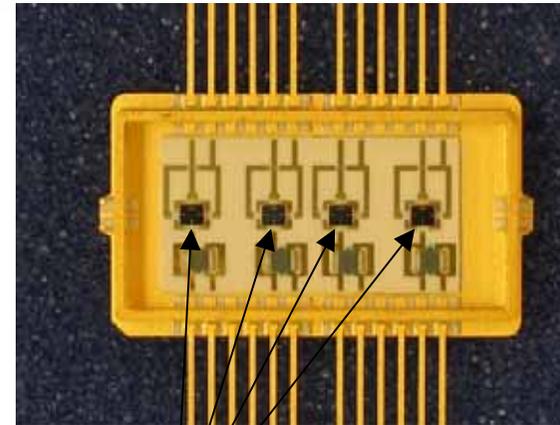
•**EMC environment** : SB4000 spécification S000330 Ed 03

Equipment OFF during launching

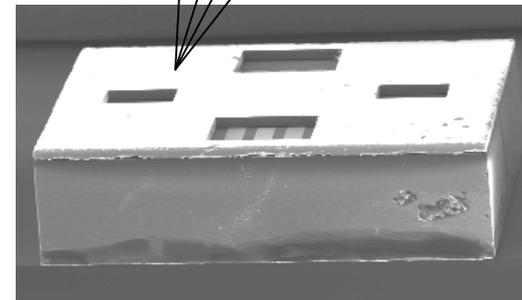
•**Radiating environment** : SB4000 specification CN11 et CN12

Al cube 0.8 mm in thickness.





Micro-package
w/ 4 MEMS



**Manufactured MEMS Demonstrator
(EM)**

Example of TC used for demonstrator operation:

| 16 bits Serial command (CS16) | | | | | | | | | | | | | | | Actions | | | | | |
|-------------------------------|----|----|----|----|-------------|----|-----|----|---------|-----|--------------------|-----|----------------------|------------|---------------------|-----|---|-------------------------------|---|----------------------|
| @FPGA | | | | | CMI | | | | COM ID | | | | | P | | | | | | |
| b0 | b1 | b2 | b3 | b4 | b5 | b6 | b7 | b8 | b9 | b10 | b11 | b12 | b13 | b14 | | b15 | | | | |
| @ FPGA | | | | | 1 0 0 0 | | | | n° Mode | | 0 0 | | 0 0 | | on/off | | P | TC-START/STOP Modes(x) | | |
| | | | | | | | | | 0 | | | | | | 0 | | | 0 | 1 | TC-STOP Mode(1) (x2) |
| | | | | | | | | | 1 | | | | | | 1 | | | 1 | 1 | TC-START Mode(1) |
| | | | | | 1 | | 1 | | 1 | 1 | TC-START-A Mode(2) | | | | | | | | | |
| | | | | | 1 | | 1 | | 1 | 1 | TC-START-B Mode(2) | | | | | | | | | |
| | | | | | 1 | | 1 | | 1 | 1 | TC-START Mode(4) | | | | | | | | | |
| | | | | | 0 0 1 1 0 1 | | | | 0 0 | | 1 1 | | 0 1 | | TC-START Gen | | | TC-START-GEN | | |
| | | | | | 1 0 1 0 | | | | 0 0 | | 0 0 | | 0 0 | | n°bus | | | Val. bus | | TC-CPC(x) |
| | | | | | 0 | | 1 | | 0 | | 0 | | 0 | | 0 | | | 0 | | TC-CPC1(1) |
| | | | | | 1 | | 1 | | 0 | | 0 | | 1 | | 1 | | | 1 | | TC-CPC1(2) |
| | | | | | 1 | | 1 | | 0 | | 0 | | 1 | | 1 | | | 0 | | TC-CPC1(3) |
| | | | | | 1 | | 1 | | 0 | | 0 | | 1 | | 1 | | | 1 | | TC-CPC1(4) |
| | | | | | 1 | | 1 | | 0 | | 0 | | 1 | | 1 | | | 0 | | TC-CPC2(1) |
| | | | | | 1 | | 1 | | 0 | | 0 | | 1 | | 1 | | | 0 | | TC-CPC2(2) |
| | | | | | 1 | | 1 | | 0 | | 0 | | 1 | | 1 | | | 0 | | TC-CPC2(3) |
| 1 | | 1 | | 0 | | 0 | | 1 | | 1 | | 1 | | TC-CPC2(4) | | | | | | |
| 1 | | 1 | | 0 | | 0 | | 1 | | 1 | | 0 | | TC-CPC3(1) | | | | | | |
| 1 | | 1 | | 0 | | 0 | | 1 | | 1 | | 1 | | TC-CPC3(2) | | | | | | |
| 1 | | 1 | | 0 | | 0 | | 1 | | 1 | | 0 | | TC-CPC3(3) | | | | | | |
| 1 | | 1 | | 0 | | 0 | | 1 | | 1 | | 1 | | TC-CPC3(4) | | | | | | |
| 1 | | 1 | | 0 | | 0 | | 1 | | 1 | | 0 | | TC-CPC4(1) | | | | | | |
| 1 | | 1 | | 0 | | 0 | | 1 | | 1 | | 1 | | TC-CPC4(2) | | | | | | |
| 1 | | 1 | | 0 | | 0 | | 1 | | 1 | | 0 | | TC-CPC4(3) | | | | | | |
| 1 | | 1 | | 0 | | 0 | | 1 | | 1 | | 1 | | TC-CPC4(4) | | | | | | |
| 1 1 1 0 | | | | | 1 0 | | 1 0 | | 1 0 | | 1 0 | | TC-INIT | | | | | | | |
| 1 1 1 1 | | | | | 0 1 | | 0 1 | | 0 1 | | 0 1 | | TC-RESET (x2) | | | | | | | |

- New equipment developed aiming at prove in-orbit operation
 - Autonomous, interface to the platform is flight proven
 - Compatible with GEO telecom platform
 - SB4000 from Thales or E*3000 from Astrium
- Functionality of EM validated, passed the standard procedure applied to commercial satellite equipment (EMC, thermal vacuum, vibration/chocs)
- FM produced, waiting the end of the RF MEMS qualification

- Know-how increased on how to implement RF MEMS into FM space equipments